

ShenZhen ChipSourceTek Technology Co. , Ltd.



FM8648M

Features

- Broadband frequency range: 0.4 to 6.0GHz
- Only one supply voltage needed
- MIPI RFFE V2.1 compatible Interface
- Compact 1.1mm x 1.1mm x 0.5mm LGA-9 package, MSL3

Applications

• 2G/3G/4G/5G antenna TRX switch

Description

The FM8648M is a CMOS silicon-on-insulator (SOI),

0.4 to 6.0GHz SP4T Switch with MIPI

SP4T transmitting and receiving switch. The high linearity performance and low insertion loss makes the device an ideal choice for GSM/WCDMA/LTE handset and data card applications.

The FM8648M is compatible with MIPI RFFE V2.1 control, which is a key requirement for many cellular transceivers. This part is packaged in a compact 1.1mm x 1.1mm x 0.5mm LGA package, which allows for a small solution size with no need for external DC blocking capacitors (when no external DC is applied to the device ports).

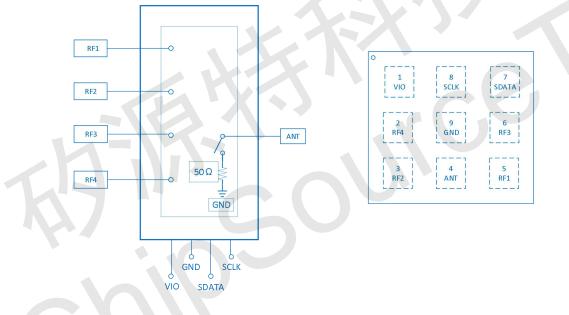


Figure 1. Functional Block Diagram and Pin Configuration Top View



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Function Characteristics

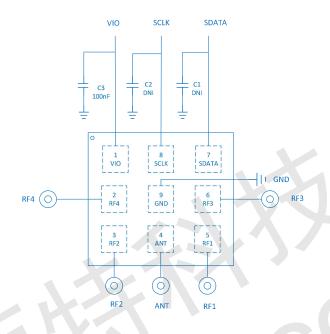


Figure 2. FM8648M Application Circuit

Table 1. Pin Descriptions

NO.	Name	Description	NO.	Name	Description
1	VIO	Supply Voltage	6	RF3	RF Port3
2	RF4	RF Port4	7	SDATA	RFFE Data
			1	SDATA	Bus
3	RF2	RF Port2	8	SCLK	RFFE Clock
			0	SOLK	Bus
4	ANT	Antenna Port	9	GND	Ground
5	RF1	RF Port1			

Table 2. Register_0 Truth Table for RF Operating Modes

Mode				Regis	ter_0			
	D7	D6	D5	D4	D3	D2	D1	D0
All RF Paths Isolated	0	0	0	0	0	0	0	0
RF1 ON	0	0	0	0	0	0	0	1
RF2 ON	0	0	0	0	0	0	1	0
RF3 ON	0	0	0	0	0	1	0	0
RF4 ON	0	0	0	0	1	0	0	0





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Electrical Characteristics

Table 3. Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit	Condition
Supply Voltage	V _{IO}	-0.3	2.5		T A=25 ℃
RFFE Bus Voltage (SDATA,	VI	-0.3	2.5	V	T A=25 ℃
SCLK)					
Max RF Input Power	P _{IN}		38	dBm	F0=950MHz, 20% DC, VIO=1.8V,
(ANT to RF1/2/3/4)					ZO=50Ω,
					TA=25 ℃
Device Operating Temperature	T _{OP}	-40	90	°C	
Device Storage Temperature	T _{STG}	-55	150		
Electrostatic Discharge(All Pins)	V _{ESD(HBM)}	1		kV	Human Body Model
	V _{ESD(CDM)}	1			Charged Device Model

Note:

Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device.

Table 4. Recommended Operating Conditions

Parameter	Symbol	MIN	TYP	MAX	Unit
Operating Frequency	Fo	0.4		6.0	GHz
Supply Voltage	V _{IO}	1.65	1.80	1.95	
RFFE Bus Voltage(SDATA, SCLK) High	V _{IH}	0.8*VIO	VIO	VIO	V
RFFE Bus Voltage(SDATA, SCLK) Low	V _{IL}	0	0	0.2*VIO	



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Table 5. Nominal O	oerating Paran	neters				
Parameter	Symbol		ecificatio	n	Unit	Condition
	Cynisol	MIN	TYP	MAX	Onit	
Normal Condition	Vi∩=1.8V_Vi				l IBm VS	l SWR=1:1, TA=25℃, Unless Otherwise Stated
			erforman			
			80	100		Active State
Supply Current	lio		6	10	μA	Low Power State
		Timin	g Perforr			
Switching Time (One						
On Path to Another)	TSW		2	3		Switching CMD 50% SCLK to 90%/10% RF
			_	10		End of Low Power State
Wakeup Time	TWK		5	10		50% SCLK to 90% RF
Turn On Time	TON			20	μs	Cold Start, 50% VIO to 90% RF
VIO Reset Time	TVIO_RST	10				VIO Off to it starts to re-power up
		RF P	erforman	ces		
			0.40	0.45		F0=0.4 to 1.0GHz
Insertion Loss			0.45	0.50		F0=1.0 to 2.0GHz
(ANT to			0.50	0.55		F0=2.0 to 3.0GHz
RF1/2/3/4)	IL		0.55	0.65		F0=3.0 to 3.8GHz
			0.65	0.90		F0=4.8 to 6.0GHz
		40	42			F0=0.4 to 1.0GHz
Isolation		38	40			F0=1.0 to 2.0GHz
	ISO	33	35			F0=2.0 to 3.0GHz
(ANT to RF1/2/3/4)		28	30		dB	F0=3.0 to 3.8GHz
		21	24			F0=4.8 to 6.0GHz
Input Return Loss	RL	12	15			F0=0.4 to 2.7GHz
(ANT to RF1/2/3/4)	KL	10	13			F0=2.7 to 6.0GHz
Input 0.1dB						
Compression						
Point (ANT to	P0.1dB		38		dBm	F0=950MHz, 20% DC
RF1/2/3/4)						
2nd Order			-90	-85		F0=950MHz @26dBm
Harmonic (ANT to	2F0		-85	-80		F0=950MHz @35dBm
RF1/2/3/4)	2FU		-85	-80		F0=1800MHz @32dBm
3rd Order			-92	-88		F0=950MHz @26dBm
Harmonic (ANT to	3F0		-85	-80	dBc	F0=950MHz @35dBm
RF1/2/3/4)			-85	-80		F0=1800MHz @32dBm





0.4 to 6.0GHz SP4T Switch with MIPI

MIPI RFFE Read and Write Timing

MIPI RFFE supports the following Command Sequences:

- Register Write
- Register Read
- Register_0 Write

Figure 3 and Figure 4 illustrate the timing diagrams for register write command sequence and read command sequence, respectively. Figure 5 describes the Register_0 write command sequence. In the below timing figures, SA[3:0] is the slave address. A[4:0] is the

register address. D[7:0] is the data. "P" is a parity bit.

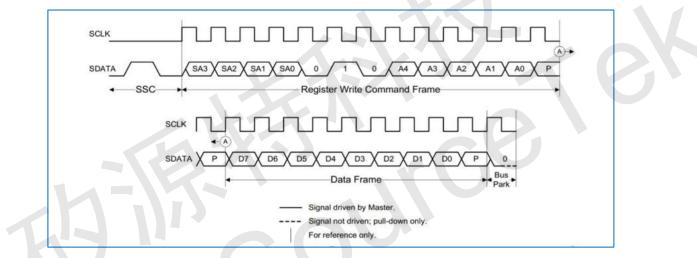


Figure 3 Register Write Command Sequence

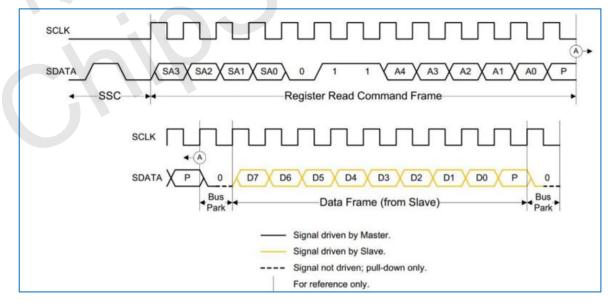


Figure 4 Register Read Command Sequence





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Figure 5 shows the Register_0 Write Command Sequence. The Command Sequence starts with an SSC, followed by the Register 0 Write Command Frame containing the Slave address, a logic '1' (to denote the command type and address), and a only seven- bit word to be written into Register 0. The Command Sequence ends with a Bus Park Cycle.

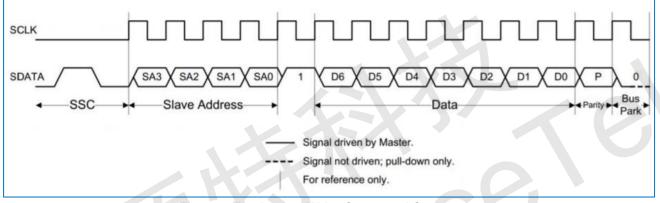


Figure 5 Register_0 Write Command Sequence

Other information such as MIPI RFFE USID programming sequence, MIPI RFFE bus specifications, etc. can

be referred to the MIPI Alliance Specification for RF Front-End Control Interface (RFFE), V2.1.



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Register Definition

Table 6. Register Definition Table

	Register Denni							
Register Address	Register Name	Data Bits	R/W	Function	Description	Default	BROADC AST_ID support	
0x00	REGISTER_0	7:0	R/W	RF Control	Register_0 truth Table: Table 2	0x00	No	Yes
0x1C	PM_TRIG	7	R/W	PWR_MODE_1	0b0: Normal Operation Mode Write Value:0b0, Read Value:0b0 0b1: Low Power Mode	060	Yes	No
					Write Value:0b1, Read Value:0b1			
		6	R/W	PWR_MODE_0	0b0: Normal Operation (ACTIVE) 0b1: Reset all registers to default settings (STARTUP) Write value: 0b1, Read Value: 0b0	0b0		0
		5	R/W	Trigger_Mask_2	0b0: Trigger_2 enabled 0b1: Trigger_2 disabled	0b0	No	No
		4	R/W	Trigger_Mask_1	0b0: Trigger_1 enabled 0b1: Trigger_1 disabled	0b0	No	No
		3	R/W	Trigger_Mask_0	0b0: Trigger_0 enabled 0b1: Trigger_0 disabled	0b0	No	No
		Trigg goes Othe	ger is o s direct erwise,	lisabled, in that cas tly to the destinatio	Trigger Masks is set to a logic ' se data written to a register ass in register. k is enabled (via a logic '0'), inc	ociated	with the	Trigger
				-	changed until its corresponding	Trigger	is assert	ed.
		2	W	Trigger_2	0b0: Keep its associateddestination registersunchanged0b1: Load its associateddestination registers withthe data in the parallel	0b0	Yes	No
					shadow register, provided Trigger_Mask_2 is			



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					0.4 10 0.0002 3641	Switci		
					disabled(Logic '0')			
					0b0: Keep its associated			
					destination registers			
		1	W	Trigger_1	unchanged	0b0	Yes	No
				00 <u>–</u>	0b1: Load its associated			
					destination registers with			
					the data in the parallel			
					shadow register, provided			
					Trigger_Mask_1 is			
					disabled(Logic '0')			
					0b0: Keep its associated			
					destination registers			
		0	w	Trigger_0	unchanged	0b0	Yes	No
					0b1: Load its associated			
					destination registers with			
				4	the data in the parallel			
					shadow register, provided			
					Trigger_Mask_0 is			
					disabled(Logic '0')			
0x1D	PRODUCT_ID	7:0	R	PRODUCT_ID	Product Number	0x72	No	No
0x1E	MANUFACTU	7:0	R	MANUFACTURE	Lower eight bits of MIPI	0x78	No	No
	RER_ID			R_ID[7:0]	registered			
					Manufacturer ID			
0x1F	MAN_USID	7:6	R	RESERVED		0b00	No	No
		5:4	R	MANUFACTURE	Upper two bits of MIPI	0x2	No	No
				R_ID[9:8]	registered			
					Manufacturer ID			
		3:0	R/W	USID	Unique Slave Address	0x8	No	No
	I			I	I			





0.4 to 6.0GHz SP4T Switch with MIPI

MIPI RFFE Operating Sequences

Here are some recommendations for MIPI RFFE operating sequences to prevent the device from damage.

- 1) Basic Operational Sequences
- Power On -- Apply Supply (VIO)-> Apply MIPI RFFE Bus (SCLK & SDATA) -> Apply RF Signal
- Power Off -- Remove RF Signal-> Remove MIPI RFFE Bus (SCLK & SDATA)->Remove Supply (VIO)

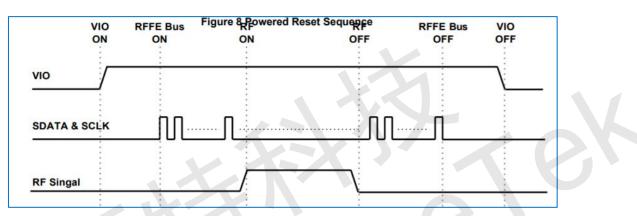


Figure 6 Basic Power On and Power Off Sequence

2) There shall be at least TON before RF power can be applied to any RF Path

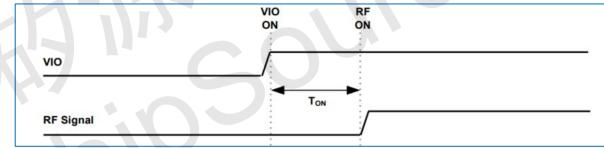


Figure 7 Supply and RF Signal On Sequence

3) Once VIO is off, there shall be at least TRST before VIO is allowed to repower on again.

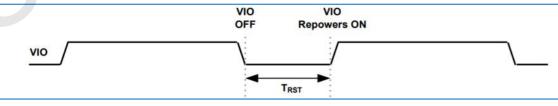


Figure 8 Supply and RF Signal On Sequence



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4) If RF signal is to be switched from one RF path to another or some paths to others, RF signal shall not be applied during such switching events to protect the devices. Hence, RF signal shall be removed before the switching command is implemented. RF signal shall not be applied before waiting at least TSW.

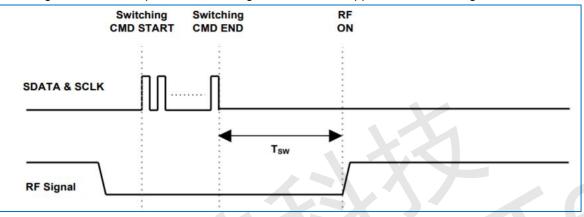


Figure 9 RF Path Switching Sequence

5) RF Signal shall not be applied during low power state. Hence, RF signal shall be removed before device enters low power state. After the state is switched from low power to active, there shall be at least TWK before the RF signal can be applied

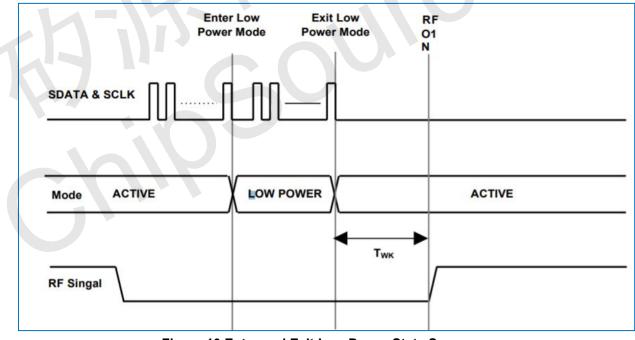


Figure 10 Enter and Exit Low Power State Sequence

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Reflow

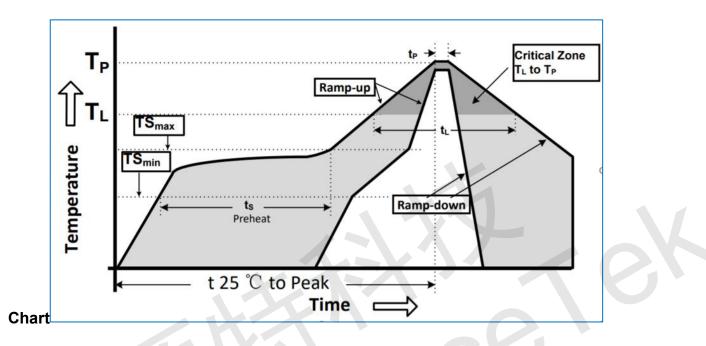


Figure 11 Recommended Lead-Free Reflow Profile

Table 7. Reflow Chart Parameters

Reflow Profile	Parameter		
Preheat Temperature(TSMIN to TSMAX)	150℃ to 200℃		
Preheat Time(ts)	60 to 180 Seconds		
Ramp-Up Rate(TSMAX to TP)	3℃/s MAX		
Time Above TL 217℃(tL)	60 to 150 Seconds		
Peak Temperature(TP)	260 ℃		
Time within 5℃ of Peak Temperature(tP)	20 to 40 Seconds		
Ramp-Down Rate(TSMAX to TP)	6℃/s MAX		
Time for 25°C to Peak Temperature(t25-TP)	8 Minutes MAX		

ESD Sensitivity

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be applied when devices are operated.

RoHS Compliant

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.